

# KS54AHCT 266

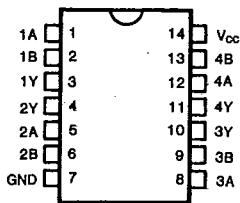
## KS74AHCT 266

### Quad Exclusive-NOR Gates with Open-Drain Outputs

#### FEATURES

- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- High-Drive-Current outputs:  
 $I_{OL} = 8 \text{ mA} @ V_{OL} = 0.5\text{V}$
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
KS74AHCT:  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$   
KS54AHCT:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

#### PIN CONFIGURATION



#### FUNCTION TABLE

| Inputs |   | Output |
|--------|---|--------|
| A      | B | Y      |
| L      | L | H      |
| L      | H | L      |
| H      | L | L      |
| H      | H | H      |

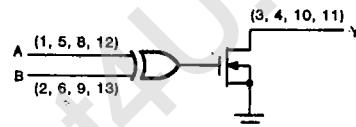
#### DESCRIPTION

These devices contain four independent exclusive-NOR gates with open-drain outputs. Using a suitable pull-up resistor, these outputs may be connected to other open-drain outputs to implement wired-AND functions.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

#### LOGIC DIAGRAM



SAMSUNG SEMICONDUCTOR

**KS54AHCT 266  
KS74AHCT****Quad Exclusive-NOR Gates  
with Open-Drain Outputs****Absolute Maximum Ratings\***

|   |                 |
|---|-----------------|
| Supply Voltage Range, V <sub>CC</sub> . . . . .   | -0.5V to +7V    |
| DC Input Diode Current, I <sub>IK</sub><br>(V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> + 0.5V) . . . . .  | ±20 mA          |
| DC Output Diode Current, I <sub>OK</sub><br>(V <sub>O</sub> < -0.5V or V <sub>O</sub> > V <sub>CC</sub> + 0.5V) . . . . . | ±20 mA          |
| Continuous Output Current Per Pin, I <sub>O</sub><br>(-0.5V < V <sub>O</sub> < V <sub>CC</sub> + 0.5V) . . . . .          | ±35 mA          |
| Continuous Current Through<br>V <sub>CC</sub> or GND pins . . . . .   | ±125 mA         |
| Storage Temperature Range, T <sub>STG</sub> . . . . .   | -65°C to +150°C |
| Power Dissipation Per Package, P <sub>D†</sub> . . . . .  | 500 mW          |

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
Plastic Package (N): -12mW/°C from 65°C to 85°C  
Ceramic Package (J): -12mW/°C from 100°C to 125°C

**Recommended Operating Conditions**

|   |   |
|---|---|
| Supply Voltage, V <sub>CC</sub> . . . . .                                 | 4.5V to 5.5V  |
| DC Input & Output Voltages*, V <sub>IN</sub> , V <sub>OUT</sub> . . . . . | 0V to V <sub>CC</sub>                                 |
| Operating Temperature   |   |
| Range   | KS74AHCT: -40°C to +85°C<br>KS54AHCT: -55°C to +125°C |
| Input Rise & Fall Times, t <sub>R</sub> , t <sub>F</sub> . . . . .        | Max 500 ns  |

\* Unused inputs must always be tied to an appropriate logic voltage level (either V<sub>CC</sub> or GND)

**DC ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub>=5V±10% Unless Otherwise Specified)

| Characteristic                       | Symbol           | Test Conditions   | T <sub>A</sub> =25°C | KS74AHCT                       |                                 | KS54AHCT          |            | Unit |
|--------------------------------------|------------------|---|----------------------|--------------------------------|---------------------------------|-------------------|------------|------|
|                                      |                  |   | Typ                  | T <sub>A</sub> =-40°C to +85°C | T <sub>A</sub> =-55°C to +125°C | Guaranteed Limits | Unit       |      |
| Minimum High-Level Input Voltage     | V <sub>IH</sub>  |   |                      | 2.0                            | 2.0                             | 2.0               | 2.0        | V    |
| Maximum Low-Level Input Voltage      | V <sub>IL</sub>  | *   |                      | 0.8                            | 0.8                             | 0.8               | 0.8        | V    |
| Maximum Low-Level Output Voltage     | V <sub>OL</sub>  | V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub><br>I <sub>O</sub> =20µA<br>I <sub>O</sub> =4mA<br>I <sub>O</sub> =8mA | 0                    | 0.1<br>0.26<br>0.39            | 0.1<br>0.33<br>0.5              | 0.1<br>0.4        | 0.1<br>0.4 | V    |
| Maximum Input Current                | I <sub>IN</sub>  | V <sub>IN</sub> =V <sub>CC</sub> or GND   |                      | ±0.1                           | ±1.0                            | ±1.0              | ±1.0       | µA   |
| Maximum Output Leakage Current       | I <sub>OZ</sub>  | V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub><br>V <sub>OUT</sub> =V <sub>CC</sub>                                  |                      | ±0.5                           | ±5.0                            | ±10.0             | ±10.0      | µA   |
| Maximum Quiescent Supply Current     | I <sub>CC</sub>  | V <sub>IN</sub> =V <sub>CC</sub> or GND<br>I <sub>OUT</sub> =0µA  |                      | 2.0                            | 20.0                            | 40.0              | 40.0       | µA   |
| Additional Worst Case Supply Current | ΔI <sub>CC</sub> | per input pin<br>V <sub>I</sub> =2.4V<br>other Inputs:<br>at V <sub>CC</sub> or GND<br>I <sub>OUT</sub> =0µA              |                      | 2.7                            | 2.9                             | 3.0               | 3.0        | mA   |

**AC ELECTRICAL CHARACTERISTICS** (Input t<sub>r</sub>, t<sub>f</sub>≤2 ns), AHCT266

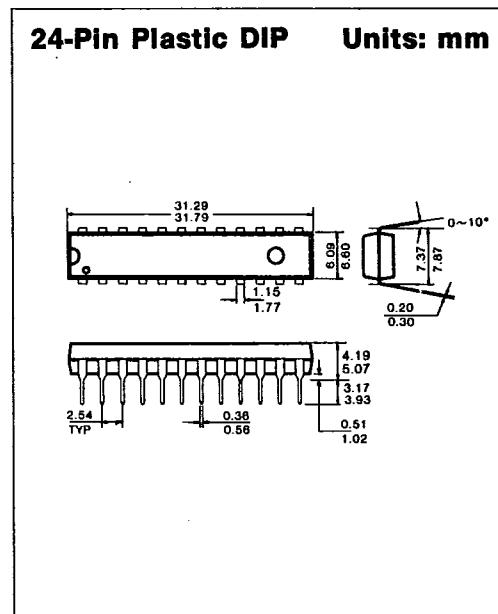
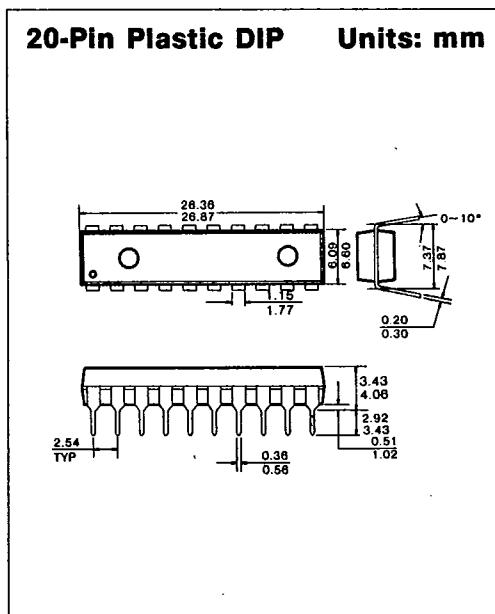
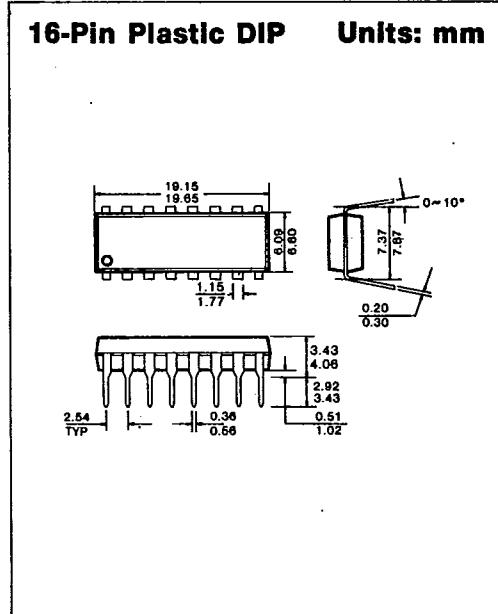
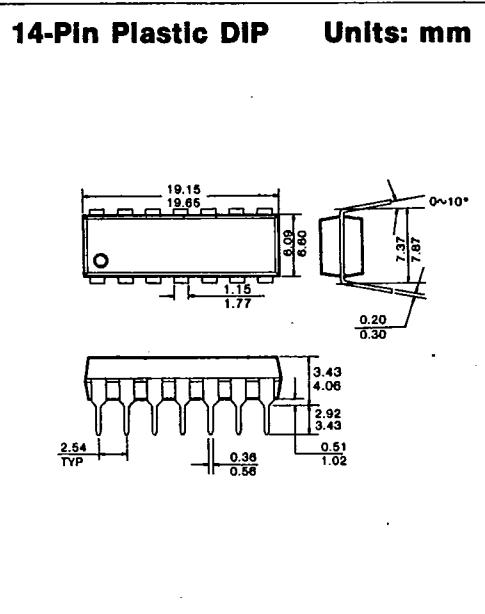
| Characteristic                 | Symbol           | Conditions†          | T <sub>A</sub> =25°C  | KS74AHCT                       |                           | KS54AHCT                        |                           | Unit |
|--------------------------------|------------------|----------------------|-----------------------|--------------------------------|---------------------------|---------------------------------|---------------------------|------|
|                                |                  |                      | V <sub>CC</sub> =5.0V | T <sub>A</sub> =-40°C to +85°C | V <sub>CC</sub> =5.0V±10% | T <sub>A</sub> =-55°C to +125°C | V <sub>CC</sub> =5.0V±10% |      |
| Propagation Delay              | t <sub>PLH</sub> | C <sub>L</sub> =50pF | 19                    |                                | 29                        |                                 | 35                        | ns   |
|                                | t <sub>PHL</sub> | R <sub>L</sub> =1kΩ  | 11                    |                                | 18                        |                                 | 22                        |      |
| Input Capacitance              | C <sub>IN</sub>  |                      | 5                     |                                |                           |                                 |                           | pF   |
| Power Dissipation Capacitance* | C <sub>PD</sub>  | (per gate)           | 15                    |                                |                           |                                 |                           | pF   |

\* C<sub>PD</sub> determines the no-load dynamic power dissipation: P<sub>D</sub>=C<sub>PD</sub> V<sub>CC</sub><sup>2</sup> f + I<sub>CC</sub> V<sub>CC</sub>.

† For AC switching test circuits and timing waveforms see section 2.



SAMSUNG SEMICONDUCTOR

**PACKAGE DIMENSIONS**T-90-20**1. PLASTIC PACKAGES**

7

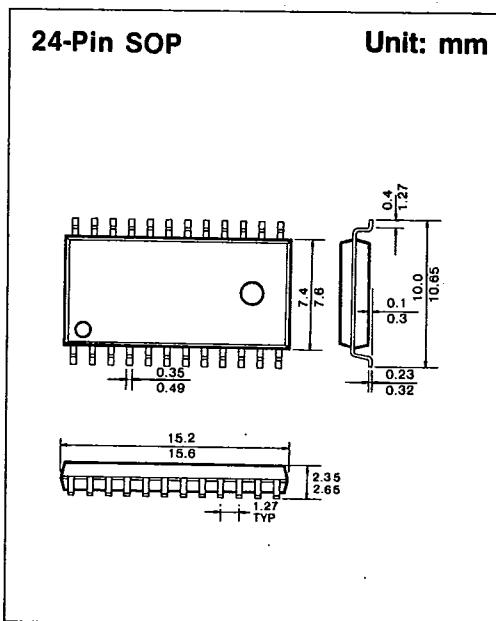
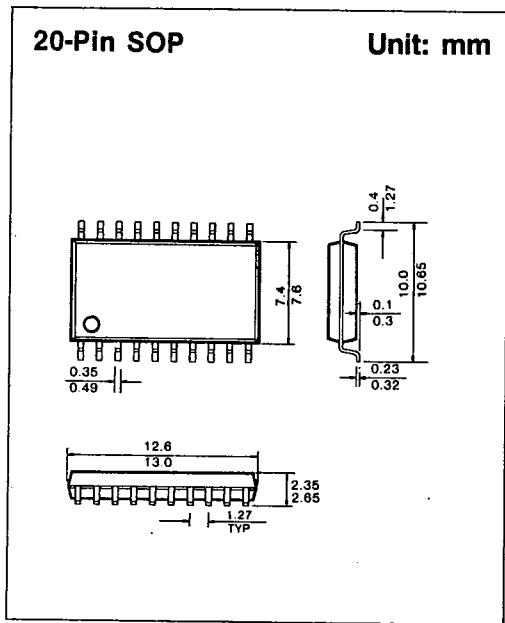
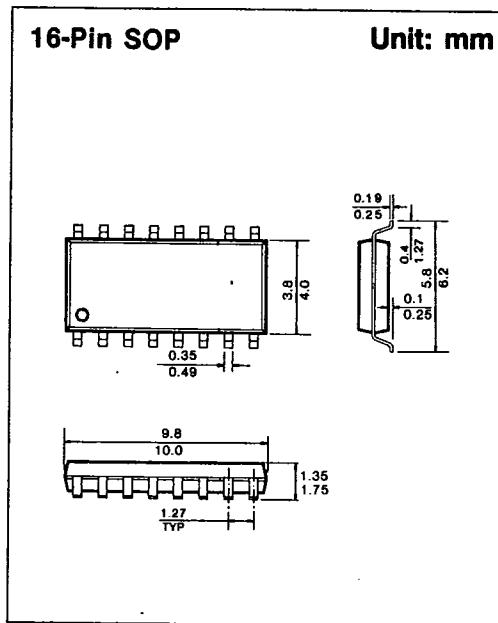
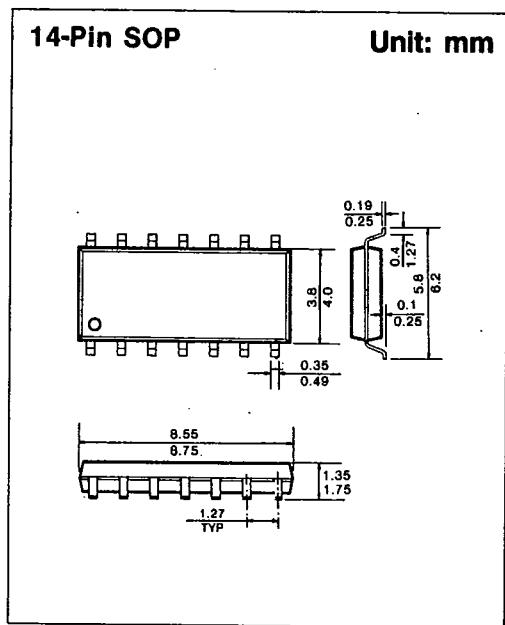


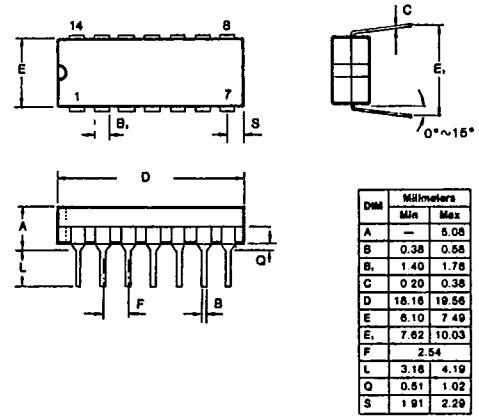
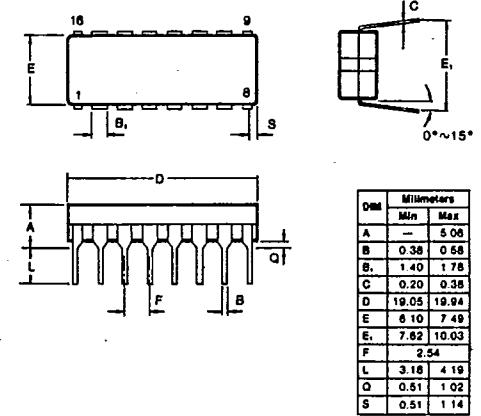
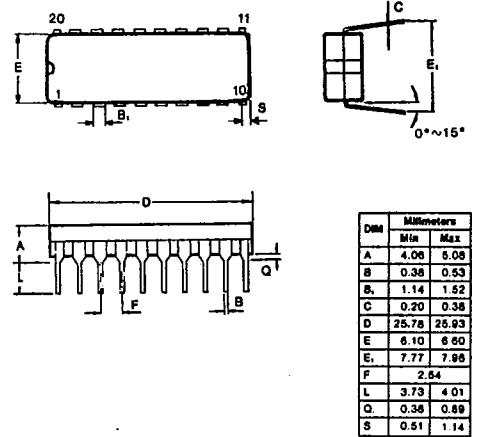
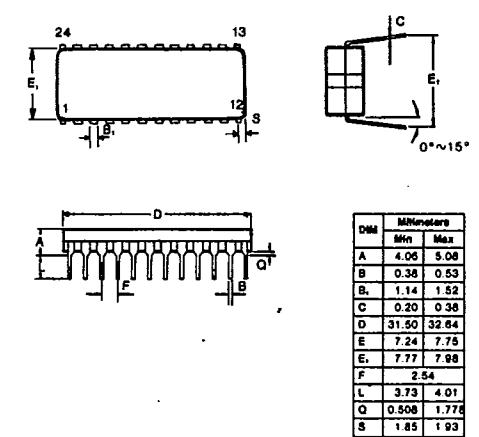
SAMSUNG SEMICONDUCTOR

1675

A-04

781

**PACKAGE DIMENSIONS****T-90-20****SAMSUNG SEMICONDUCTOR****1676****A-05****782**

**PACKAGE DIMENSIONS**T-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

7